

Precision, Micropower, Single Supply Instrumentation Amplifier (Fixed Gain = 10 or 100)

FEATURES

■ Gain Error	0.04% Max
■ Gain Non-Linearity	0.0008% (8ppm) Max
■ Gain Drift	4ppm/°C Max
■ Supply Current	105μA Max
■ Offset Voltage	160 _μ V Max
 Offset Voltage Drift 	0.4μV/°C Typ
Offset Current	600pA Max
■ CMRR, G = 100	100dB Min
0.1Hz to 10Hz Noise	0.9 _μ Vp-p Typ
	2.3pAp-p Typ
Gain Bandwidth Product	250kHz Min

APPLICATIONS

■ Single or Dual Supply Operation

■ Surface Mount Package Available

- Differential Signal Amplification in Presence of Common-Mode Voltage
- Micropower Bridge Transducer Amplifier
 - Thermocouples
 - Strain Gauges
 - Thermistors
- Differential Voltage to Current Converter
- **Transformer Coupled Amplifier**
- 4mA-20mA Bridge Transmitter

DESCRIPTION

The LT1101 establishes the following milestones:

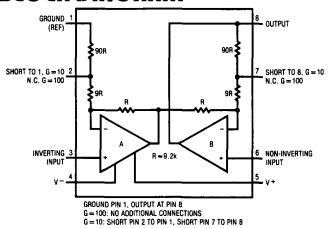
- (1) It is the first micropower instrumentation amplifier,
- (2) It is the first single supply instrumentation amplifier,
- (3) It is the first instrumentation amplifier to feature fixed gains of 10 and/or 100 in low cost, space-saving 8-lead packages.

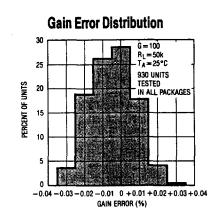
The LT1101 is completely self-contained: no external gain setting resistor is required. The LT1101 combines its micropower operation (75_µA supply current) with a gain error of 0.008%, gain linearity of 3ppm, gain drift of 1ppm/°C. The output is guaranteed to drive a 2k load to $\pm 10V$ with excellent gain accuracy.

Other precision specifications are also outstanding: 50µV input offset voltage, 130pA input offset current, and low drift $(0.4\mu\text{V/}^{\circ}\text{C})$ and $0.7\text{pA/}^{\circ}\text{C}$. In addition, unlike other instrumentation amplifiers, there is no output offset voltage contribution to total error.

A full set of specifications are provided with $\pm 15V$ dual supplies and for single 5V supply operation. The LT1101 can be operated from a single lithium cell or two Ni-Cad batteries. Battery voltage can drop as low as 1.8V, yet the LT1101 still maintains its gain accuracy. In single supply applications, both input and output voltages swing to within a few millivolts of ground. The output sinks current while swinging to ground — no external, power consuming pull down resistors are needed.

BLOCK DIAGRAM



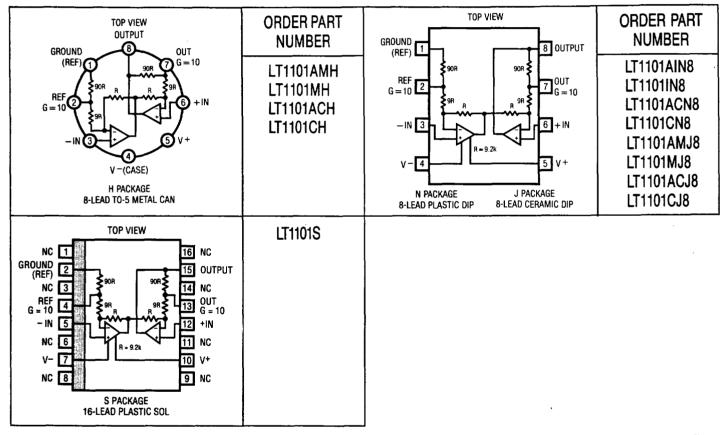


ABSOLUTE MAXIMUM RATINGS

Supply Voltage	V
Differential Input Voltage ± 36	V
Input Voltage Equal to Positive Supply Voltag	е
10V Below Negative Supply Voltage	е
Output Short Circuit Duration Indefinit	е
Lead Temperature (Soldering, 10 sec.)300°	0

Operating Temperature Range	
LT1101AM/LT1101M	– 55°C to 125°C
LT1101AI/LT1101I	40°C to 85°C
LT1101AC/LT1101C/LT1101S	0°C to 70°C
Storage Temperature Range	
All Grades	65°C to 150°C

PACKAGE/ORDER INFORMATION



ELECTRICAL CHARACTERISTICS

 $V_S = 5V$, 0V, $V_{CM} = 0.1V$, $V_{REF(PIN 1)} = 0.1V$, G = 10 or 100, $T_A = 25$ °C, unless otherwise noted (Note 3).

			LT1	101AM/	M/AC				
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
G _E	Gain Error	G = 100, V _O = 0.1V to 3.5V, R _L = 50k G = 10, V _O = 0.1V to 3.5V, R _L = 50k		0.010 0.009	0.050 0.040		0.011 0.010	0.075 0.060	% %
G _{NL}	Gain Non-Linearity	G = 100, R _L = 50k G = 10, R _L = 50k (Note 1)		20 3	60 7		20 3	75 8	ppm ppm
Vos	Input Offset Voltage	LT1101S		50	160		60 250	220 600	μV μV
los	Input Offset Current		T	0.13	0.60		0.15	0.90	nA
l _B	Input Bias Current			6	8		6	10	nA
Is	Supply Current			75	105		78	120	μА

ELECTRICAL CHARACTERISTICS

 $V_S = 5V$, 0V, $V_{CM} = 0.1V$, $V_{REF(PIN 1)} = 0.1V$, G = 10 or 100, $T_A = 25$ °C, unless otherwise noted (Note 3).

SYMBOL CMRR			LT1	101AM/	AVAC				
	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
	Common-Mode Rejection Ratio	1k Source imbalance G = 100, V _{CM} = 0.07V to 3.4V G = 10, V _{CM} = 0.07V to 3.1V	95 84	106 100		92 82	105 99		dB dB
	Minimum Supply Voltage	(Note 4)		1.8	2.3		1.8	2.3	V
V _o	Maximum Output Voltage Swing	Output High, 50k to GND Output High, 2k to GND Output Low, V _{REF} = 0, No Load Output Low, V _{REF} = 0, 2k to GND Output Low, V _{REF} = 0, I _{SINK} = 100 _# A	4.1 3.5	4.3 3.9 3.3 0.5 90	6 1 130	4.1 3.5	4.3 3.9 3.3 0.5 90	6 1 130	V V mV mV
BW	Bandwidth	G = 100 (Note 1) G = 10 (Note 1)	2.0 22	3.0 33	•	2.0 22	3.0 33		kHz kHz
SR	Slew Rate	(Note 1)	0.04	0.07		0.04	0.07		V/μS

ELECTRICAL CHARACTERISTICS

 $V_S = \pm 15V$, $V_{CM} = 0V$, $T_A = 25$ °C, Gain = 10 or 100, unless otherwise noted.

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
GE	Gain Error	$G = 100, V_0 = \pm 10V, R_L = 50k$		0.008	0.040		0.009	0.060	%
•		$G = 100, V_0 = \pm 10V, R_L = 2k$		0.011	0.055		0.012	0.070	%
		$G = 10, V_O = \pm 10V, R_L = 50k \text{ or } 2k$		0.008	0.040		0.009	0.060	%
G _{NL}	Gain Non-Linearity	$G = 100, R_L = 50k$		7	16		8	20	ppm
		G = 100, R _L = 2k		24 3	45 8	ŀ	25 3	60 9	ppm
14	les A Official Value for	G = 10, R _L = 50k or 2k	<u> </u>	 50	160	 	60	220	ppm μV
Vos	Input Offset Voltage	LT1101S		50	160		90 250	600	μV μV
laa .	Input Offset Current	LETIOIS		0.13	0.60		0.15	0.90	nA
los	Input Bias Current			6	8		6	10	nA
I _B	 		 		-0			- 10	117
	Input Resistance Common-Mode	(Note 1)	4	7		3	7		GΩ
	Differential Mode	(Note 1)	7	12		5	12		GΩ
e _n	Input Noise Voltage	0.1Hz to 10Hz (Note 2)		0.9	1.8		0.9		μVр-р
<u> </u>	Input Noise Voltage	f _a = 10Hz (Note 2)		45	64		45		nV/√Hz
	Density	$f_0 = 1000 Hz (Note 2)$		43	54		43		nV/√Hz
in	Input Noise Current	0.1Hz to 10Hz (Note 2)		2.3	4.0		2.3		рАр-р
	Input Noise Current	f _o = 10Hz (Note 2)		0.06	0.10		0.06		pA/√ <u>H</u> z
	Density	f _o = 1000Hz		0.02			0.02		pA/√Hz
	Input Voltage Range	G = 100	+ 13.0	+ 13.8		+ 13.0	+ 13.8		l v
		2 42	- 14.4	- 14.7		- 14.4	- 14.7		Į v
		G = 10	+ 11.5 - 13.0	+ 12.5 - 13.3		+11.5	+ 12.5 - 13.3		V
CMRR	Common-Mode	1k Source Imbalance	10.0						
Omm	Rejection Ratio	G = 100, Over CM Range	100	112		98	112		dB
		G = 10, Over CM Range	84	100		82	99		dB
PSRR	Power Supply Rejection Ratio	$V_S = +2.2V, -0.1V \text{ to } \pm 18V$	102	114		100	4145		dB
Is	Supply Current			92	130		94	150	μΑ
Vo	Maximum Output	R _L = 50k	± 13.0	± 14.2		±13.0	± 14.2		V
-	Voltage Swing	R _L = 2k	± 11.0	± 13.2		±11.0	± 13.2		V
BW	Bandwidth	G = 100 (Note 1)	2.3	3.5		2.3	3.5		kHz
		G = 10 (Note 1)	25	37		25	37		kHz
SR	Slew Rate		0.06	0.10		0.06	0.10		VIμs

Note 1: This parameter is not tested. It is guaranteed by design and by inference from other tests.

Note 2: This parameter is tested on a sample basis only.

Note 3: These test conditions are equivalent to $V_S = 4.9V$, -0.1V, $V_{CM} = 0V$, $V_{REF(PIN 1)} = 0V$.

Note 4: Minimum supply voltage is guaranteed by the power supply rejection test. The LT1101 actually works at 1.8V supply with minimal degradation in performance.



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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
G _E	Gain Error	$G = 100, V_0 = \pm 10V, R_1 = 50k$		0.024	0.070		0.026	0.100	%
-		$G = 100, V_0 = \pm 10V, R_L = 5k$		0.030	0.100		0.035	0.130	%
		$G = 10, V_0 = \pm 10V, R_L = 50k \text{ or } 5k$	1	0.015	0.070		0.018	0.100	%
TCGE	Gain Error Drift	$G = 100, R_L = 50k$		2	4		2	5	ppm/°C
	(Note 1)	$G = 100, R_L = 5k$		2	7	İ	2	8	ppm/°C
		$G = 10, R_L = 50k \text{ or } 5k$		1	4		1	5	ppm/°C
G _{NL}	Gain Non-Linearity	$G = 100, R_L = 50k$		24	70		26	90	ppm
		$G = 100, R_L = 5k$		70	300		75	500	ppm
		$G = 10, R_L = 50k$	1	4	13		5	15	ppm
		G = 10, R _L = 5k	ļ	10	40		12	60	ppm
Vos	Input Offset Voltage			90	350		110	500	μV
ΔV _{OS} /ΔT	Input Offset Voltage Drift	(Note 1)		0.4	2.0		0.5	2.8	μV/°C
los	Input Offset Current			0.16	0.80		0.19	1.30	nA
Δl _{OS} /ΔT	Input Offset Current Drift	(Note 1)		0.5	4.0		0.8	7.0	pA/°C
l _B	Input Bias Current			7	10		7	12	nA
ΔΙ _Β /ΔΤ	Input Bias Current Drift	(Note 1)		10	25		10	30	pA/°C
CMRR	Common-Mode	$G = 100, V_{CM} = -14.4V \text{ to } 13V$	96	111		94	111		dB
	Rejection Ratio	$G = 10, V_{CM} = -13V \text{ to } 11.5V$	80	99		78	98		dB
PSRR	Power Supply Rejection Ratio	$V_S = +3.0, -0.1V \text{ to } \pm 18V$	98	110		94	110		dB
Is	Supply Current			105	165		108	190	μА
$\overline{v_0}$	Maximum Output	R _L = 50k	± 12.5	± 14.0		± 12.5	±14.0		٧
	Voltage Swing	R _L =5k	±11.0	± 13.5		± 11.0	± 13.5		V

ELECTRICAL CHARACTERISTICS $V_S = \pm 15V, V_{CM} = 0V, Gain = 10 \text{ or } 100, 0^{\circ}C \le T_A \le 70^{\circ}C, unless otherwise noted.$

				LT1101AC					
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
GE	Gain Error	$G = 100, V_0 = \pm 10V, R_L = 50k$		0.012	0.055		0.014	0.080	%
		$G = 100, V_0 = \pm 10V, R_L = 2k$	1	0.018	0.085		0.020	0.100	%
		$G = 10, V_0 = \pm 10V, R_L = 50k \text{ or } 2k$		0.009	0.055		0.010	0.080	%
TCGE	Gain Error Drift	G = 100, R _L = 50k		1	4		1	5	ppm/°C
	(Note 1)	G = 100, R _L = 2k		2	7		2	9	ppm/°C
		G = 10, R _L = 50k or 2k		1	4		1	_5	ppm/°C
G _{NL}	Gain Non-Linearity	$G = 100, R_L = 50k$		9	25		10	35	ppm
		$G = 100, R_L = 2k$		33	75		36	100	ppm
		$G = 10, R_L = 50k \text{ or } 2k$		4	10		4	11	ppm
Vos	Input Offset Voltage			70	250		85	350	۷بر
		LT1101S					300	800	μ۷
$\Delta V_{OS}/\Delta T$	Input Offset Voltage Drift	(Note 1)		0.4	2.0		0.5	2.8	μV/°C
		LT1101S					1.2	4.5	μV/°C
los	Input Offset Current			0.14	0.70		0.17	1.10	nA
$\Delta l_{OS}/\Delta T$	Input Offset Current Drift	(Note 1)		0.5	4.0		0.8	7.0	pA/°C
l _B	Input Bias Current			6	9		6	11	nA
ΔΙ _Β /ΔΤ	Input Bias Current Drift	(Note 1)		10	25		10	30	ρΑ/°C
CMRR	Common-Mode	G = 100, V _{CM} = - 14.4V to 13V	98	112		96	112		dB
	Rejection Ratio	G = 10, V _{CM} = - 13V to 11.5V	82	100		80	99		₫B
PSRR	Power Supply	$V_S = 2.5, -0.1V \text{ to } \pm 18V$	100	112		97	112		dB
	Rejection Ratio								
S	Supply Current			98	148		100	170	μА
V ₀ .	Maximum Output	R _L = 50k	± 12.5	± 14.1		± 12.5	± 14.1		٧
	Voltage Swing	R _L = 2k	± 10.5	± 13.0		± 10.5	± 13.0		V

ELECTRICAL CHARACTERISTICS

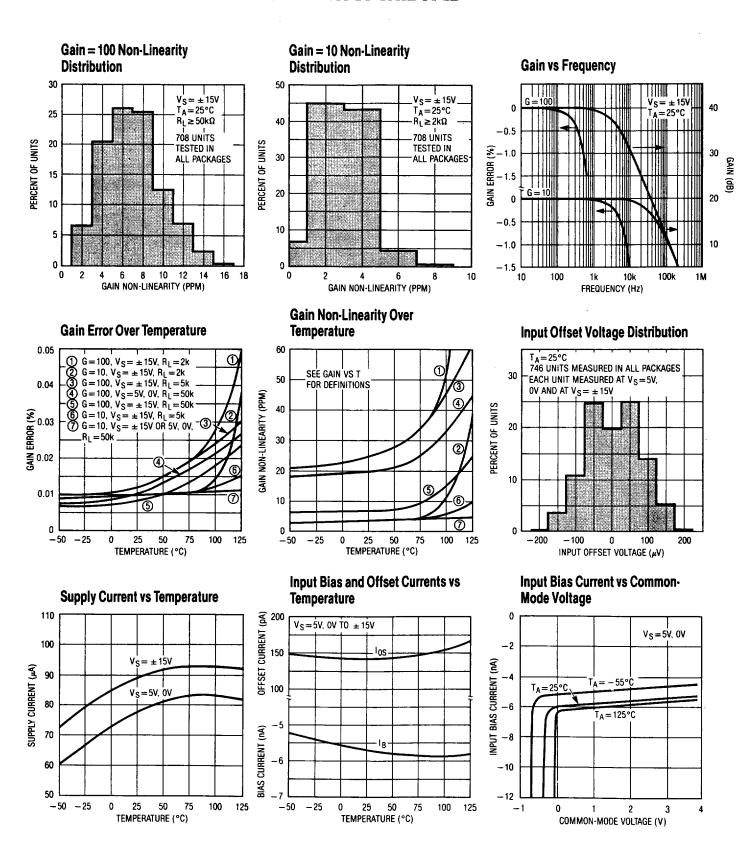
 $V_S = 5V$, 0V, $V_{CM} = 0.1V$, $V_{REF(PIN~1)} = 0.1V$, Gain = 10 or 100, $-55^{\circ}C \le T_A \le 125^{\circ}C$ for AM/M grades, $-40^{\circ}C \le T_A \le 85^{\circ}C$ for Al/I grades, unless otherwise noted.

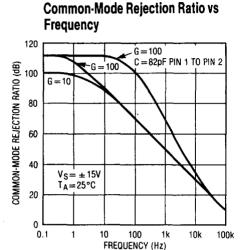
			1	T1101AN	I/AI		LT1101M	Л	
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
GE	Gain Error	G = 100, V _O = 0.1V to 3.5V, R _L = 50k G = 10, V _{CM} = 0.15, R _L = 50k		0.026 0.011	0.080 0.070		0.028 0.014	0.120 0.100	% %
TCGE	Gain Error Drift	R _L = 50k (Note 1)		1	4		1	5	ppm/°C
G _{NL}	Gain Non-Linearity	G = 100, R _L = 50k G = 10, R _L = 50k (Note 1)		45 4	110 13		48 5	140 15	ppm ppm
Vos	input Offset Voltage			90	350		110	500	μV
ΔV _{OS} /ΔT	Input Offset Voltage Drift	(Note 1)		0.4	2.0		0.5	2.8	μV/°C
los	Input Offset Current			0.16	0.80		0.19	1.30	nA
ΔI _{OS} /ΔT	Input Offset Current Drift	(Note 1)		0.5	4.0		0.8	7.0	pA/°C
l _B	Input Bias Current			7	10		7	12	nA
ΔΙ _Β /ΔΤ	Input Bias Current Drift	(Note 1)		10	25		10	30	pA/°C
CMRR	Common-Mode Rejection Ratio	G = 100, V _{CM} = 0.1V to 3.2V G = 10, V _{CM} = 0.1V to 2.9V, V _{REF} = 0.15V	91 80	105 98		88 77	104 97		dB dB
Is	Supply Current			88	135		92	160	μΑ
v _o	Maximum Output Voltage Swing	Output High, 50k to GND Output High, 2k to GND Output Low, V _{REF} = 0, No Load Output Low, V _{REF} = 0, 2k to GND Output Low, V _{REF} = 0, I _{SINK} = 100µA	3.8 3.0	4.1 3.7 4.5 0.7 125	8 1.5 170	3.8 3.0	4.1 3.7 4.5 0.7 125	8 1.5 170	V V mV mV

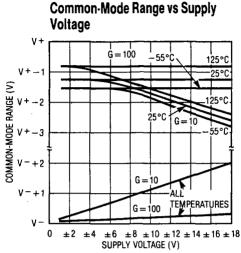
ELECTRICAL CHARACTERISTICS

 $V_S = 5V$, 0V, $V_{CM} = 0.1V$, $V_{REF(PIN~1)} = 0.1V$, Gain = 10 or 100, 0°C \leq $T_A \leq$ 70°C, unless otherwise noted.

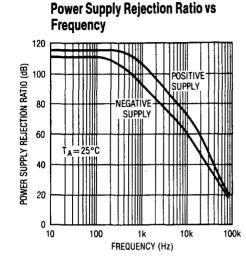
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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
G _E	Gain Error	$G = 100, V_0 = 0.1V \text{ to } 3.5V, R_L = 50k$ $G = 10, V_{CM} = 0.15V, R_L = 50k$		0.017 0.010	0.065 0.060		0.018 0.012	0.095 0.080	% %
TCGE	Gain Error Drift	R _L = 50k (Note 1)		1	4		1	5	ppm/°C
G _{NL}	Gain Non-Linearity	G = 100, R _L = 50k G = 10, R _L = 50k (Note 1)		25 4	80 10		25 4	100 11	ppm ppm
V _{OS}	Input Offset Voltage	LT1101S		70	250		85 300	350 800	μV μV
ΔV _{OS} /ΔT	Input Offset Voltage Drift	(Note 1)		0.4	2.0		0.5	2.8	μVI°C
		LT1101S					1.2	4.5	μV/°C
los	Input Offset Current			0.14	0.70		0.17	1.10	nA
ΔI _{OS} /ΔT	Input Offset Current Drift	(Note 1)		0.5	4.0		0.8	7.0	pA/°C
I _B	Input Bias Current			6	9		6	11	nA
ΔΙ _Β /ΔΤ	Input Bias Current Drift	(Note 1)		10	25		10	30	pA/°C
CMRR	Common-Mode Rejection Ratio	G = 100, V _{CM} = 0.07V to 3.3V G = 10, V _{CM} = 0.07V to 3.0V, V _{REF} = 0.15V	93 82	105 99		90 80	104 98		dB dB
Is	Supply Current			80	120		85	145	μА
V _o	Maximum Output Voltage Swing	Output High, 50k to GND Output High, 2k to GND	4.0 3.3	4.2 3.8		4.0 3.3	4.2 3.8		V
		Output Low, V _{REF} = 0, No Load	1	4	7		4	7	mV
		Output Low, V _{REF} = 0, 2k to GND Output Low, V _{REF} = 0, I _{SINK} = 100 _µ A		0.6 100	1.2 150		0.6 100	1.2 150	mV mV

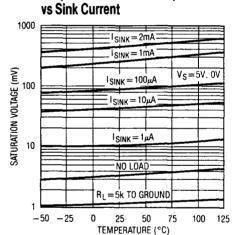




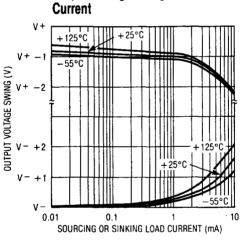


Output Voltage Swing vs Load

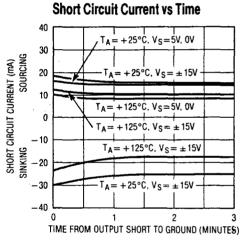


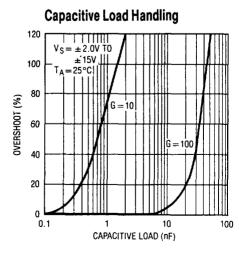


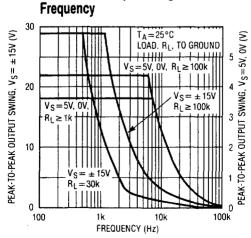
Output Saturation vs Temperature

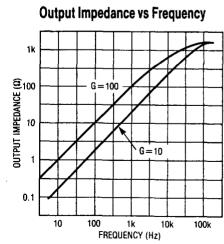


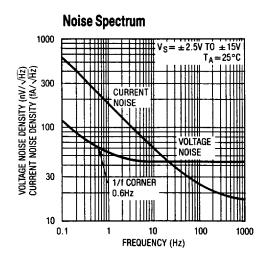
Undistorted Output Swing vs

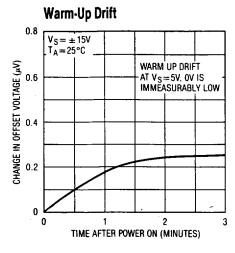


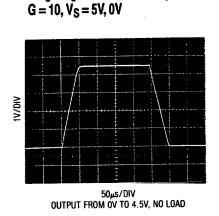












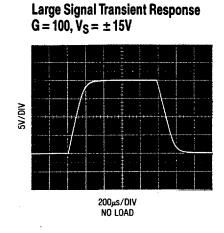
Large Signal Transient Response

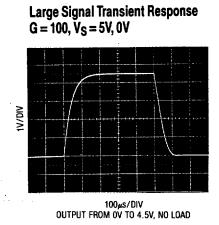
 $G = 10, V_S = \pm 15V$

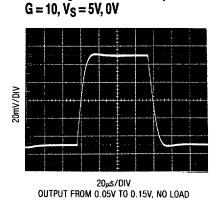
NO LOAD

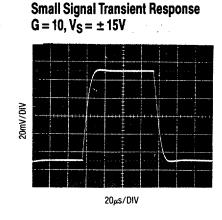
Small Signal Transient Response

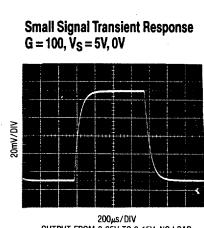
Large Signal Transient Response



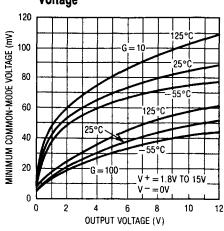




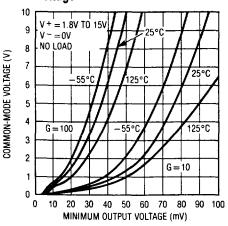


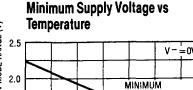


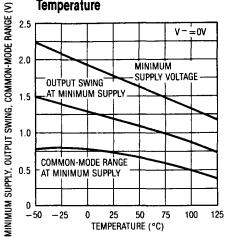
Single Supply: Minimum Common-Mode Voltage vs Output Voltage



Single Supply: Minimum Output Voltage vs Common-Mode Voltage







APPLICATIONS INFORMATION

Single Supply Applications

The LT1101 is the first instrumentation amplifier which is fully specified for single supply operation, i.e. when the negative supply is 0V. Both the input common-mode range and the output swing are within a few millivolts of ground.

Probably the most common application for instrumentation amplifiers is amplifying a differential signal from a transducer or sensor resistance bridge. All competitive instrumentation amplifiers have a minimum required common-mode voltage which is 3V to 5V above the negative supply. This means that the voltage across the bridge has to be 6V to 10V or dual supplies have to be used, i.e. micropower, single battery usage is not attainable on competitive devices.

The minimum output voltage obtainable on the LT1101 is a function of the input common-mode voltage. When the common-mode voltage is high and the output is low, current will flow from the output of amplifier A into the output of amplifier B. See the Minimum Output Voltage vs Common-Mode Voltage plot.

Similarly, the Minimum Common-Mode Voltage vs Output Voltage plot specifies the expected common-mode range. When the output is high and input common-mode is low, the output of amplifier A has to sink current coming from the output of amplifier B. Since amplifier A is effectively in unity gain, its input is limited by its output.

Common-Mode Rejection vs Frequency

The common-mode rejection ratio (CMRR) of the LT1101 starts to roll off at a relatively low frequency. However, as shown on the CMRR vs Frequency plot, CMRR can be enhanced significantly by connecting an 82pF capacitor between pins 1 and 2. This improvement is only available in the gain 100 configuration, and it is in excess of 30dB at 60Hz.

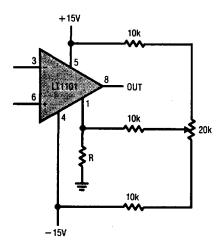
Offset Nulling

The LT1101 is not equipped with dedicated offset null terminals. In many bridge transducer or sensor applications, calibrating the bridge simultaneously eliminates the instrumentation amplifier's offset as a source of error. For example, in the Micropower Remote Temperature Sensor Application shown, one adjustment removes the offset errors due to the temperature sensor, voltage reference and the LT1101.

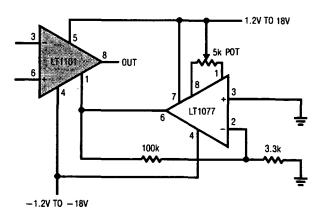


APPLICATIONS INFORMATION

A simple resistive offset adjust procedure is shown below. If $R=5\Omega$ for G=10, and $R=50\Omega$ for G=100 then the effect of R on gain error is approximately 0.006%. Unfortunately, about 450μ A has to flow through R to bias the reference terminal (pin 1) and to null out the worst-case offset voltage. The total current through the resistor network can exceed 1mA, and the micropower advantage of the LT1101 is lost.



Another offset adjust scheme uses the LT1077 micropower op amp to drive the reference pin 1. Gain error and common-mode rejection are unaffected, the total current increase is 45μ A. The offset of the LT1077 is trimmed and amplified to match and cancel the offset voltage of the LT1101. Output offset null range is \pm 25mV.



Gains Between 10 and 100

Gains between 10 and 100 can be achieved by connecting two equal resistors (= R_x) between pins 1 and 2 and pins 7 and 8.

Gain =
$$10 + \frac{R_X}{R + R_Y/90}$$

The nominal value of R is $9.2k\Omega$. The usefulness of this method is limited by the fact that R is not controlled to better than $\pm 10\%$ absolute accuracy in production. However, on any specific unit 90R can be measured between pins 1 and 2.

Input Protection

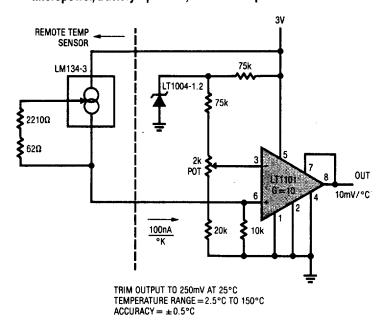
Instrumentation amplifiers are often used in harsh environments where overload conditions can occur. The LT1101 employs PNP input transistors, consequently the differential input voltage can be $\pm 30V$ (with $\pm 15V$ supplies, $\pm 36V$ with $\pm 18V$ supplies) without an increase in input bias current. Competitive instrumentation amplifiers have NPN inputs which are protected by back to back diodes. When the differential input voltage exceeds $\pm 1.3V$ on these competitive devices, input current increases to the milliampere level; more than $\pm 10V$ differential voltage can cause permanent damage.

When the LT1101's inputs are pulled above the positive supply, the inputs will clamp a diode voltage above the positive supply. No damage will occur if the input current is limited to 20mA.

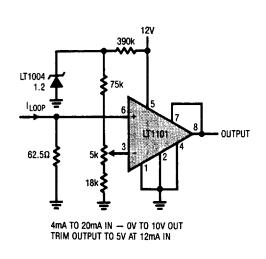
 500Ω resistors in series with the inputs protect the LT1101 when the inputs are pulled as much as 10V below the negative supply.

TAPPLICATIONS INFORMATION

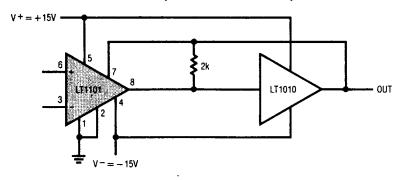
Micropower, Battery Operated, Remote Temperature Sensor



4mA to 20mA Loop Receiver

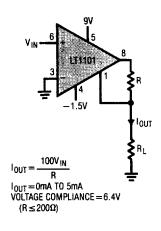


Instrumentation Amplifier with ± 150mA Output Current

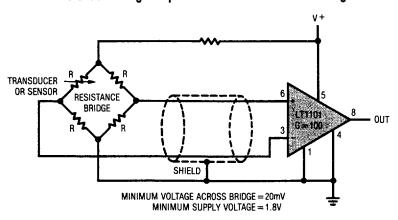


GAIN = 10, DEGRADED BY 0.01% DUE TO LT1010 OUTPUT = \pm 10V INTO 75 Ω (TO 1.5kHz) DRIVES ANY CAPACITIVE LOAD SINGLE SUPPLY APPLICATION (V + = 5V, V - = 0V): V_{OUT MIN} = 120mV, V_{OUT MAX} = 3.4V

Voltage Controlled Current Source



Differential Voltage Amplification from a Resistance Bridge





APPLICATIONS INFORMATION

Gain = 20, 110 or 200 Instrumentation Amplifiers

